

To: Customer

PCN # C&P-13-020

Date: July 1<sup>st</sup>, 2013

**TOSHIBA CORPORATION**  
**SOCIAL INFRASTRUCTURE SYSTEMS**  
**COMPANY**

Defense & Electronic Systems Div.

Components & Parts Business Development Dept.

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**PCN(Process/Product Change Notice)**  
**of Toshiba Microwave Semiconductor Products**

Dear Madams and Sirs,

We thank you very much for your continuous patronage to our Microwave Semiconductor products. Taking this opportunity, we are glad to inform you that we are going to change the specifications of the product. We therefore wish to advise you for your understanding and acceptance of this change.

Sincerely yours

— NOTE —

**1. Applicable Products:**

TGI7785-50L

**2. Description of change:**

Maximum drain current under rated output power, IDS1, to be changed from 6.0A to 6.3A

**3. Reason of change:**

Productivity improvement for manufacturing applicable Microwave Power GaN HEMT

**4. Transition Dates:**

The change will be implemented with deliveries after 3K1A (October 1<sup>st</sup>, 2013) shipping lot.

— To be continued. —

## 5. Effect of Change

There is no impact to product quality and reliability.

## 6. Contact

Revised datasheet will be available at following link.

[Microwave Semiconductor - Social Infrastructure Systems Company : Toshiba](#)

If you have further question, please contact our local Toshiba office on this matter.

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